MOSFETs Silicon N-Channel MOS (DTMOSⅤ)

# TK290P65Y

## 1. Applications

- Switching Voltage Regulators

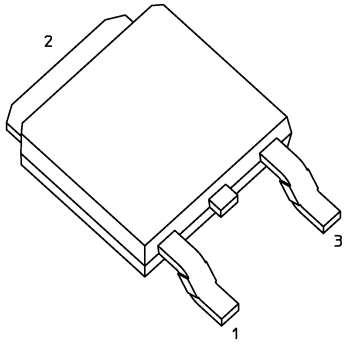
## 2. Features

(1) Low drain-source on-resistance: $R_{DS(ON)}$ = 0.23 Ω (typ.) by using Super Junction Structure : DTMOS

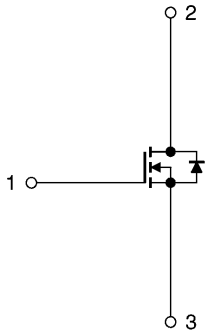
(2) Easy to control Gate switching

(3) Enhancement mode: $V_{th}$ = 3 to 4 V ($V_{DS}$ = 10 V, $I_D$ = 0.45 mA)

## 3. Packaging and Internal Circuit




DPAK




1: Gate
2: Drain
3: Source

## 4. Absolute Maximum Ratings (Note) ($T_a$ = 25 °C unless otherwise specified)

| Characteristics | | | Symbol | Rating | Unit |
|---|---|---|---|---|---|
| Drain-source voltage | | | $V_{DSS}$ | 650 | V |
| Gate-source voltage | | | $V_{GSS}$ | ±30 | |
| Drain current (DC) | ($T_c$ = 25 °C) | (Note 1) | $I_D$ | 11.5 | A |
| Drain current (DC) | ($T_c$ = 100 °C) | (Note 1) | $I_D$ | 7.3 | A |
| Drain current (pulsed) | ($T_c$ = 25 °C) | (Note 1) | $I_{DP}$ | 46 | A |
| Power dissipation | ($T_c$ = 25 °C) | | $P_D$ | 100 | W |
| Single-pulse avalanche energy | | (Note 2) | $E_{AS}$ | 106 | mJ |
| Single-pulse avalanche current | | | $I_{AS}$ | 3 | A |
| Reverse drain current (DC) | | (Note 1) | $I_{DR}$ | 11.5 | |
| Reverse drain current (pulsed) | | (Note 1) | $I_{DRP}$ | 46 | A |
| Channel temperature | | | $T_{ch}$ | 150 | °C |
| Storage temperature | | | $T_{stg}$ | -55 to 150 | °C |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production
2016-12

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## 5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|---|---|---|---|
| Channel-to-case thermal resistance | $R_{th(ch-c)}$ | 1.25 | °C/W |
| Channel-to-ambient thermal resistance | $R_{th(ch-a)}$ | 125 | |

Note 1: Ensure that the channel temperature does not exceed 150 °C.
Note 2: $V_{DD}$ = 90 V, $T_{ch}$ = 25 °C (initial), L = 20.9 mH, $R_G$ = 25 Ω, $I_{AS}$ = 3 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

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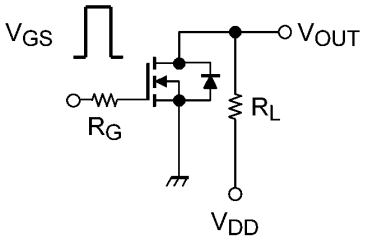
# 6. Electrical Characteristics

## 6.1. Static Characteristics ($T_a$ = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|
| Gate leakage current | $I_{GSS}$ | $V_{GS}$ = ±30 V, $V_{DS}$ = 0 V | — | — | ±1 | μA |
| Drain cut-off current | $I_{DSS}$ | $V_{DS}$ = 650 V, $V_{GS}$ = 0 V | — | — | 10 | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $I_D$ = 10 mA, $V_{GS}$ = 0 V | 650 | — | — | V |
| Gate threshold voltage | $V_{th}$ | $V_{DS}$ = 10 V, $I_D$ = 0.45 mA | 3 | — | 4 | |
| Drain-source on-resistance | $R_{DS(ON)}$ | $V_{GS}$ = 10 V, $I_D$ = 5.8 A | — | 0.23 | 0.29 | Ω |

## 6.2. Dynamic Characteristics ($T_a$ = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|
| Input capacitance | $C_{iss}$ | $V_{DS}$ = 300 V, $V_{GS}$ = 0 V, f = 100 kHz | — | 730 | — | pF |
| Reverse transfer capacitance | $C_{rss}$ | | — | 2.5 | — | |
| Output capacitance | $C_{oss}$ | | — | 26 | — | |
| Effective output capacitance | $C_{o(er)}$ | $V_{DS}$ = 0 to 400 V, $V_{GS}$ = 0 V | — | 48 | — | |
| Gate resistance | $r_g$ | $V_{DS}$ = OPEN , f = 1 MHz | — | 32 | — | Ω |
| Switching time (rise time) | $t_r$ | See Figure 6.2.1 | — | 25 | — | ns |
| Switching time (turn-on time) | $t_{on}$ | | — | 65 | — | |
| Switching time (fall time) | $t_f$ | | — | 8.5 | — | |
| Switching time (turn-off time) | $t_{off}$ | | — | 170 | — | |
| MOSFET dv/dt ruggedness | dv/dt | $V_{DS} \leq V_{(BR)DSS}$, $I_D \leq$ 5.8 A | 50 | — | — | V/ns |




$V_{DD} \approx$ 400 V
$V_{GS}$ = 10 V/0 V
$I_D$ = 5.8 A
$R_L$ = 68 Ω
$R_G$ = 10 Ω
Duty ≤ 1 %, $t_w$ = 10 μs

**Fig. 6.2.1 Switching Time Test Circuit**

## 6.3. Gate Charge Characteristics ($T_a$ = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|
| Total gate charge (gate-source plus gate-drain) | $Q_g$ | $V_{DD} \approx$ 400 V, $V_{GS}$ = 10 V, $I_D$ = 11.5 A | — | 25 | — | nC |
| Gate-source charge 1 | $Q_{gs1}$ | | — | 4 | — | |
| Gate-drain charge | $Q_{gd}$ | | — | 13 | — | |

## 6.4. Source-Drain Characteristics ($T_a$ = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|
| Diode forward voltage | $V_{DSF}$ | $I_{DR}$ = 11.5 A, $V_{GS}$ = 0 V | — | — | -1.7 | V |
| Reverse recovery time | $t_{rr}$ | $V_{DD} \approx$ 400 V<br>$I_{DR}$ = 5.8 A, $V_{GS}$ = 0 V<br>$-dI_{DR}/dt$ = 100 A/μs | — | 240 | — | ns |
| Reverse recovery charge | $Q_{rr}$ | | — | 2.3 | — | μC |
| Peak reverse recovery current | $I_{rr}$ | | — | 20 | — | A |
| Diode dv/dt ruggedness | dv/dt | $V_{DS} \leq$ 400 V, $I_{DR} \leq$ 5.8 A, $V_{GS}$ = 0 V | 15 | — | — | V/ns |

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## 7. Marking

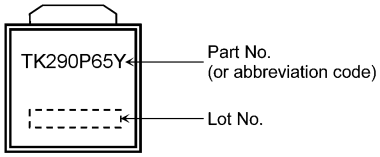



Fig. 7.1 Marking

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## 8. Characteristics Curves (Note)

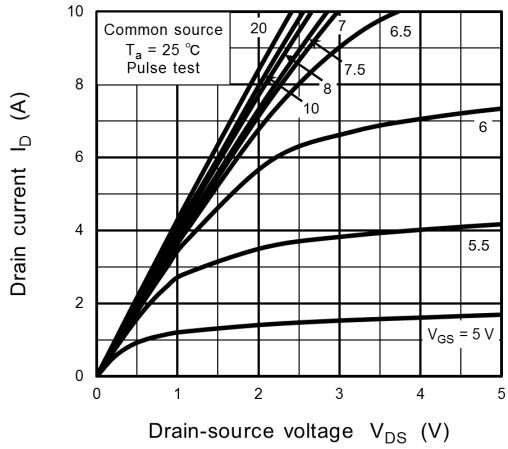



Fig. 8.1 $I_D$ - $V_{DS}$

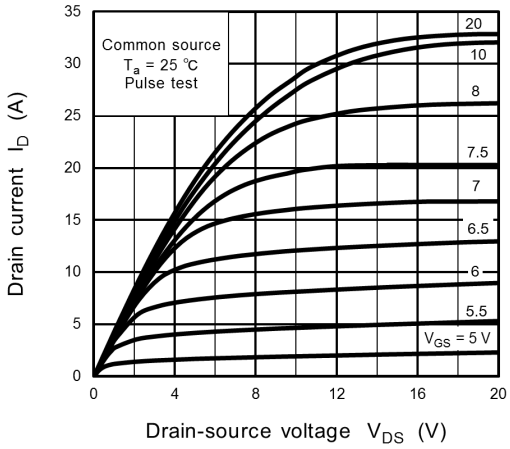



Fig. 8.2 $I_D$ - $V_{DS}$

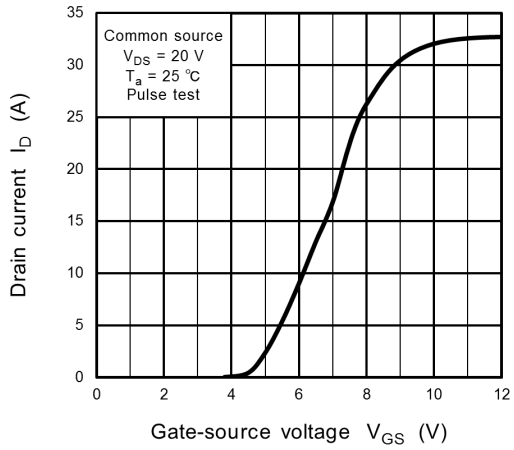



Fig. 8.3 $I_D$ - $V_{GS}$

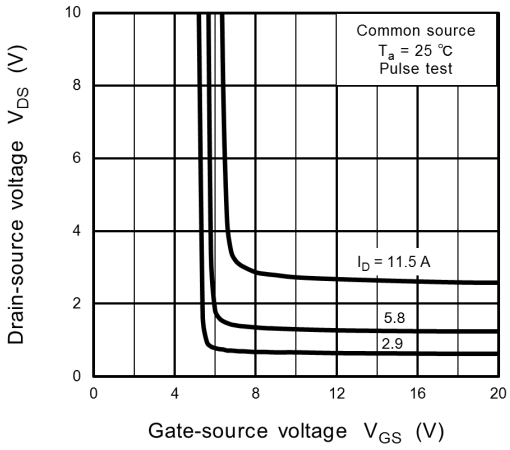



Fig. 8.4 $V_{DS}$ - $V_{GS}$

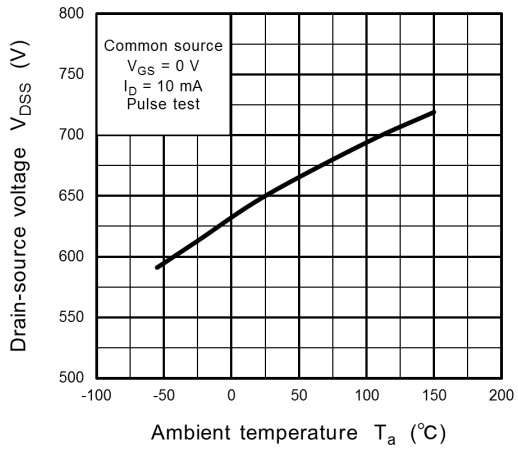



Fig. 8.5 $V_{DSS}$ - $T_a$

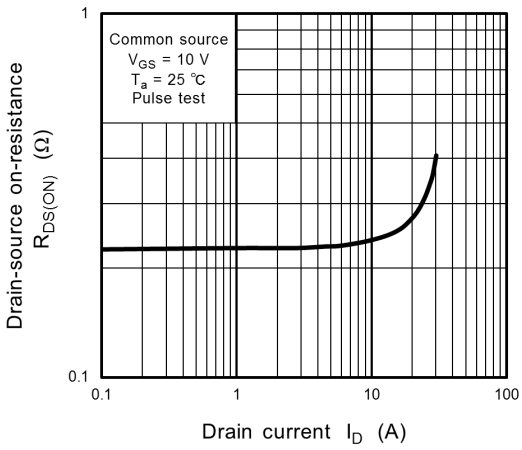



Fig. 8.6 $R_{DS(ON)}$ - $I_D$

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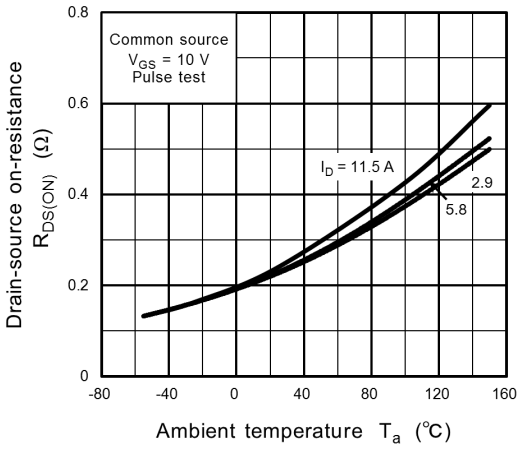



Fig. 8.7 $R_{DS(ON)}$ - $T_a$

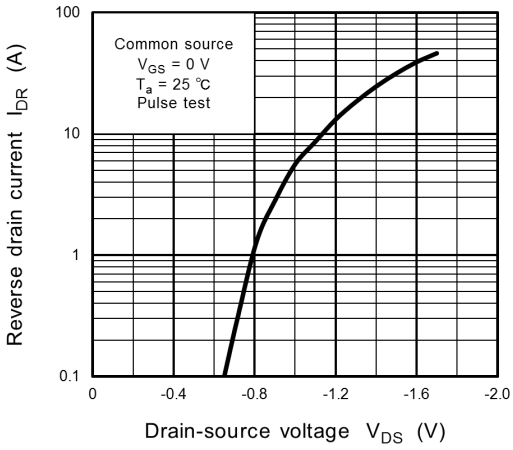



Fig. 8.8 $I_{DR}$ - $V_{DS}$

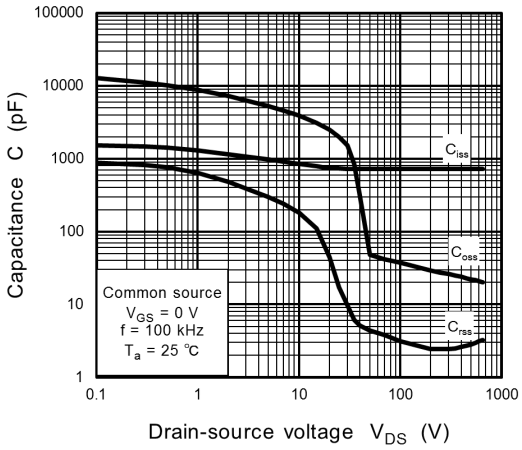



Fig. 8.9 C - $V_{DS}$

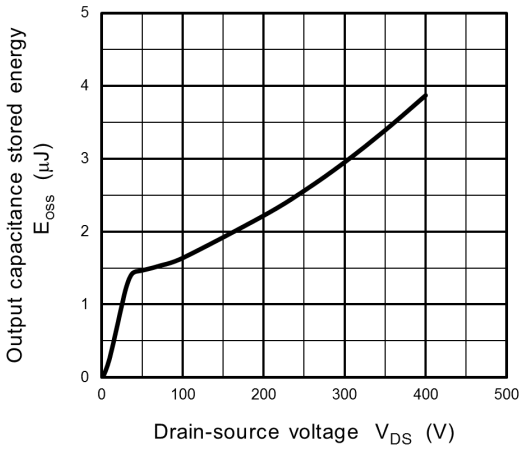



Fig. 8.10 $E_{oss}$ - $V_{DS}$

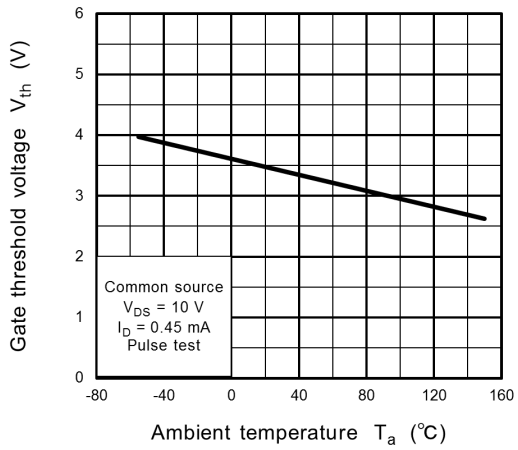



Fig. 8.11 $V_{th}$ - $T_a$

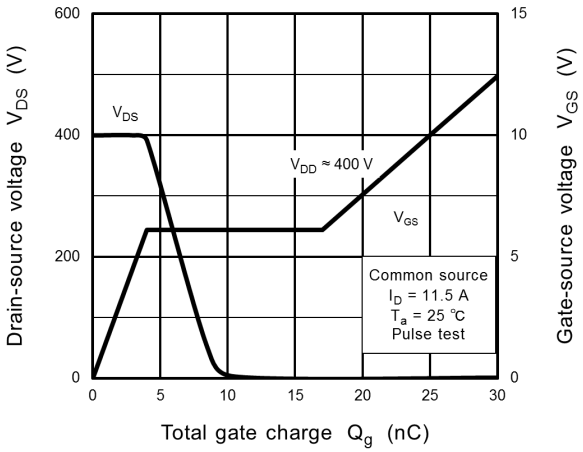



Fig. 8.12 Dynamic Input/Output Characteristics

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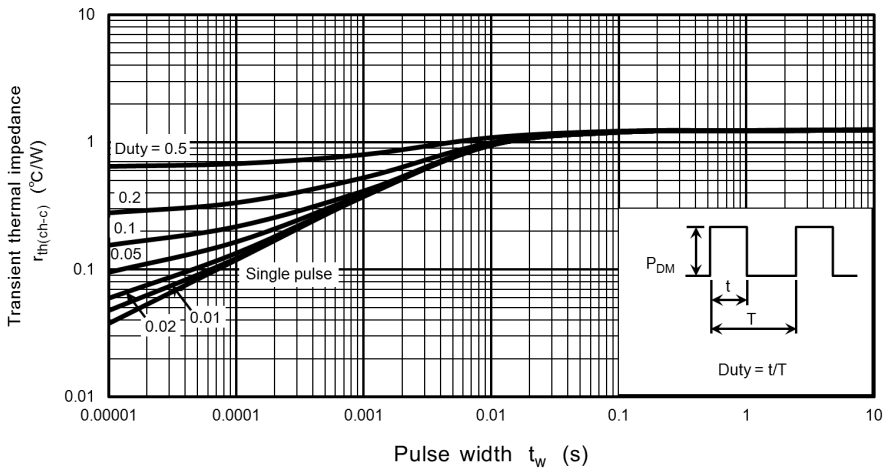



**Fig. 8.13 $r_{th}$ - $t_w$**
**(Guaranteed Maximum)**

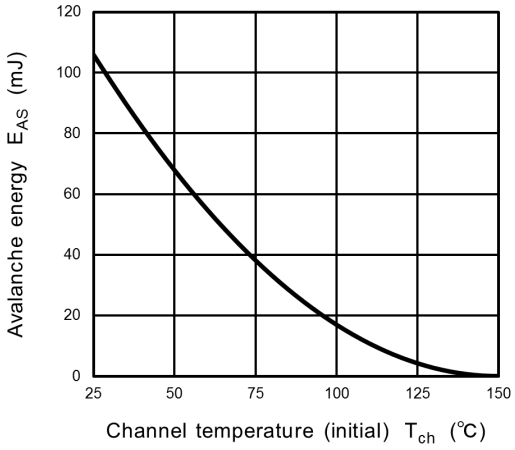



**Fig. 8.14 $E_{AS}$ - $T_{ch}$**
**(Guaranteed Maximum)**

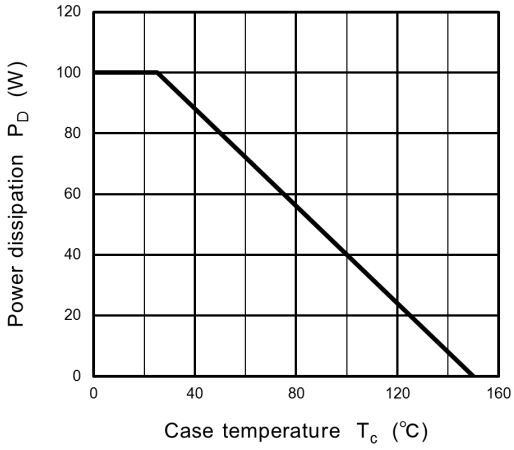
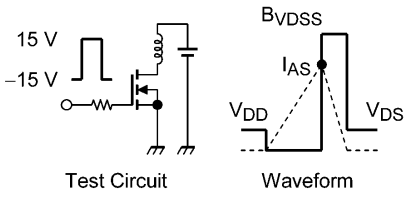



**Fig. 8.15 $P_D$ - $T_c$**
**(Guaranteed Maximum)**




$R_G = 25\ \Omega$, $V_{DD} = 90$ V $E_{AS} = \frac{1}{2} \cdot L \cdot I_{AS}^2 \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$

**Fig. 8.16 Test Circuit/Waveform**

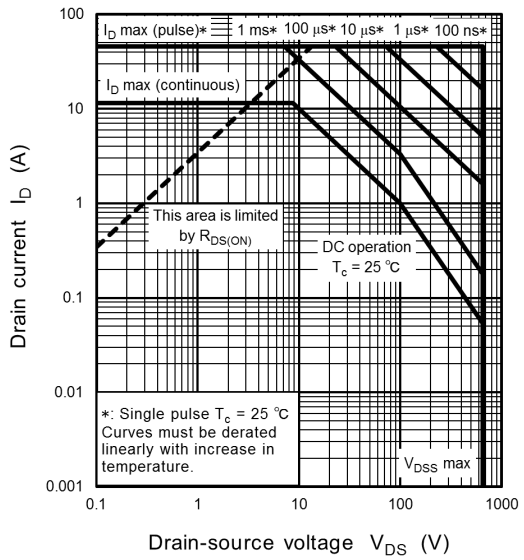
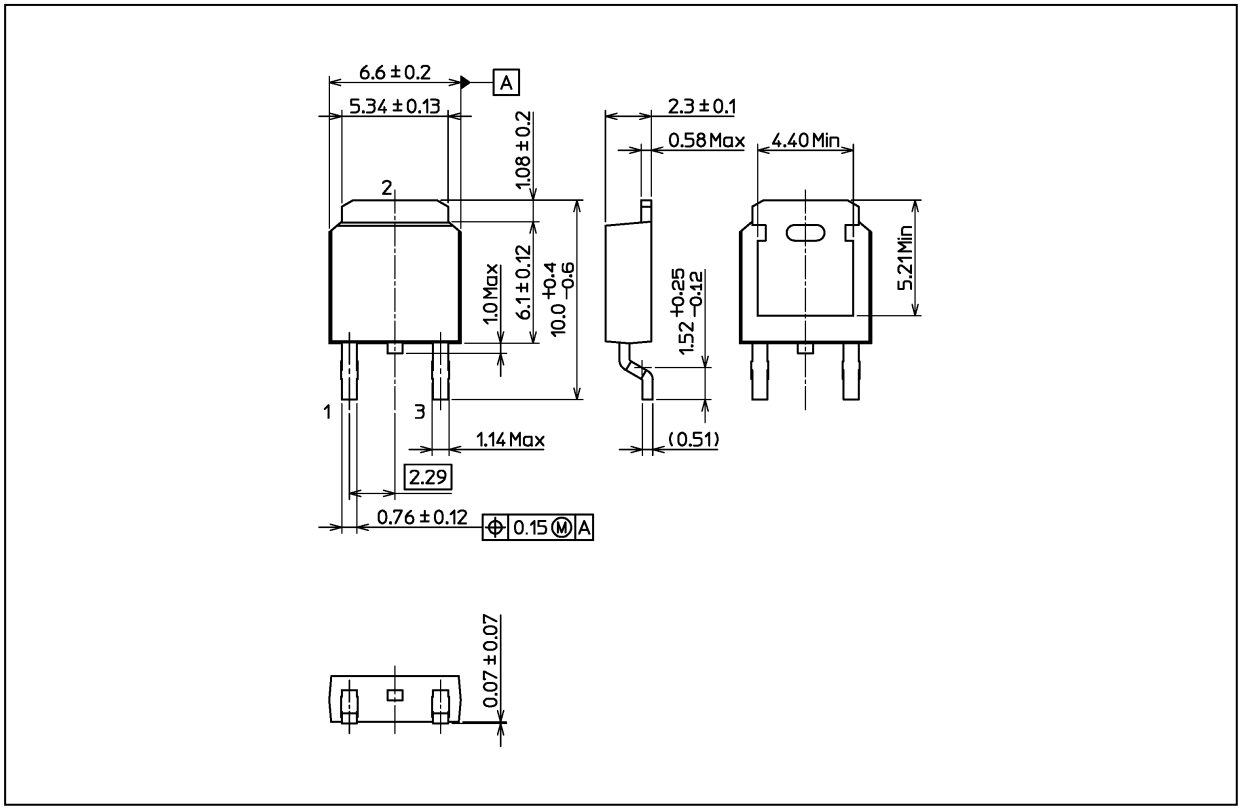



**Fig. 8.17 Safe Operating Area (Guaranteed Maximum)**

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

## Package Dimensions

Unit: mm




Weight: 0.36 g (typ.)

| Package Name(s) |
|---|
| TOSHIBA: 2-7K1S |
| Nickname: DPAK |

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